

Supporting Information

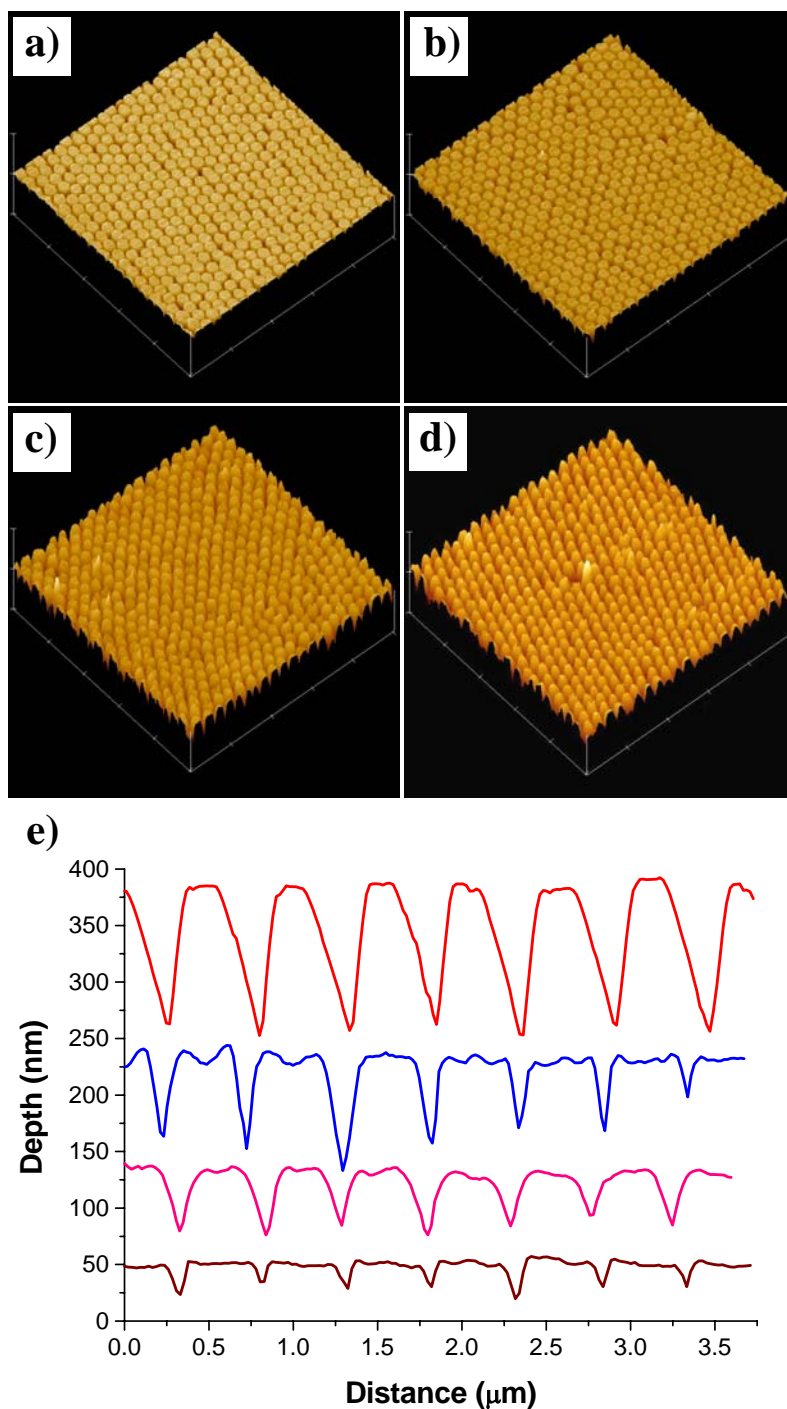


Figure S1. Contact mode AFM images and depth profiles of silicon nanopillar arrays etched under the same RIE conditions but different time. a) 4 min. b) 8 min. c) 12 min. d) 16 min. The corresponding depth profiles (from bottom to top with increasing etch time) are shown in e) and have been vertically offset for clarity.